SQJ144EP

RoHS

COMPLIANT HALOGEN

FREE

www.vishay.com

Vishay Siliconix

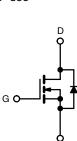
Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0046
I _D (A)	130
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40	V	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	1-	130		
Continuous drain current	T _C = 125 °C	I _D	75		
Continuous source current (diode conduction)		IS	134	А	
Pulsed drain current ^a		I _{DM}	238		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	23		
Single pulse avalanche energy	che energy		26.5	mJ	
Maximum power dissipation ^a	$T_{\rm C} = 25 ^{\circ}{\rm C}$ D 148	W			
Maximum power dissipation "	T _C = 125 °C	PD	49	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^c			260	U	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R _{thJA}	68	°C/W
Junction-to-case (drain)		R _{thJC}	1.0	C/W

Notes

b. When mounted on 1" square PCB (FR4 material)

1

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

www.vishay.com

Vishay Siliconix

SQJ144EP

SPECIFICATIONS ($T_C = 25 \ ^{\circ}C$,	unless otherv	vise noted)						
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	40	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	2.5	3.0	3.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	= 0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	250		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.0036	0.0046		
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 15 A, T _J = 125 °C	-	-	0.0074	V 0 nA μA A 6 4 8 5 0 pF nC Ω 5 nS 4 0 pF nC Ω 5 nS 2 nS	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0088		
Forward transconductance ^b	9 _{fs}	V _{DS}	= 15 V, I _D = 10 A	-	45	-	S	
Dynamic ^b					-			
Input capacitance	C _{iss}			-	1510	1960		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 V$, f = 1 MHz	-	510	665	pF	
Reverse transfer capacitance	C _{rss}	1		-	34	45		
Total gate charge ^c	Qg			-	26	36		
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 20 \text{ V}, I_{D} = 10 \text{ A}$	-	7.6	-	nC	
Gate-drain charge ^c	Q _{gd}			-	5.5	-		
Gate resistance	Rg		f = 1 MHz	2.0	3.5	5.6	Ω	
Turn-on delay time ^c	t _{d(on)}			-	11	16.5		
Rise time ^c	t _r	V _{DD}	= 20 V, R _L = 2 Ω,	-	4.4	6.2	-	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 \text{ A},$	V_{GEN} = 10 V, R_g = 1 Ω	-	21.5	30	115	
Fall time ^c	t _f			-	5.7	8		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed current ^a	I _{SM}			-	-	238	Α	
Forward voltage	V _{SD}	I _F =	15 A, V _{GS} = 0 V	-	-	1.1	V	
Body diode reverse recovery time	t _{rr}			-	28.4	40	ns	
Body diode reverse recovery charge	Q _{rr}	I 40	A, di/dt = 100 A/µs	-	15.8	22.2	nC	
Reverse recovery fall time	t _a	ı _F = 40	$A, u/u = 100 A/\mu s$	-	13.8	19.3	200	
Reverse recovery rise time	t _b]		-	14.9	20.9	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	0.94	1.3	А	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

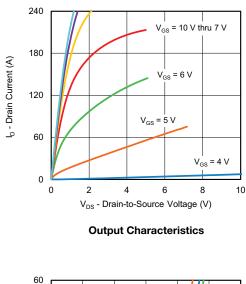
c. Independent of operating temperature

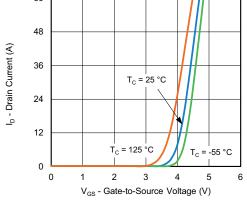
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

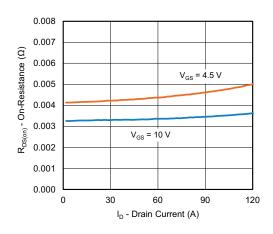


TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

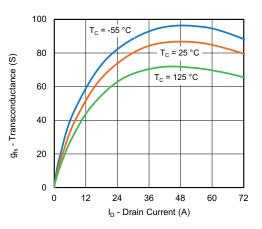




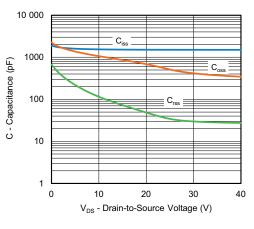
Transfer Characteristics



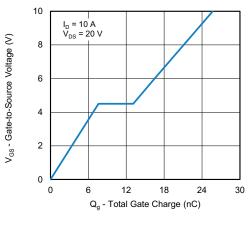
On-Resistance vs. Drain Current



Transconductance







Gate Charge

S20-0201-Rev. A, 30-Mar-2020

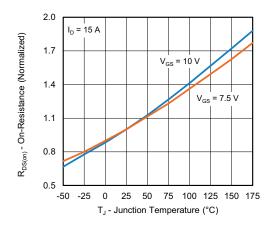
3

Document Number: 77430

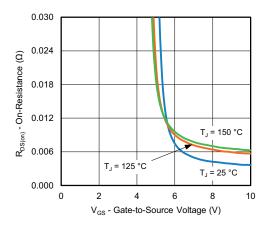
For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



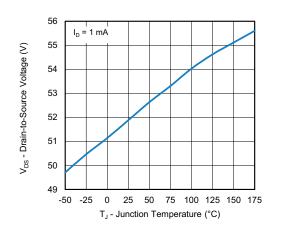
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to Source Voltage

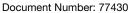


Drain Source Breakdown vs. Junction Temperature Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

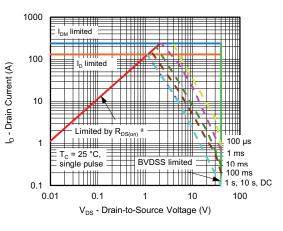
S20-0201-Rev. A, 30-Mar-2020

4

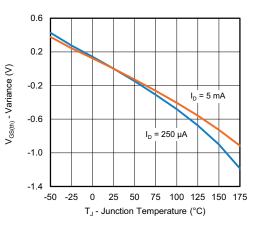


(t) transformed to the second state of the s

Source Drain Diode Forward Voltage





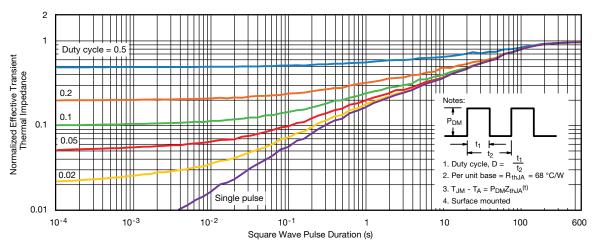


Threshold Voltage

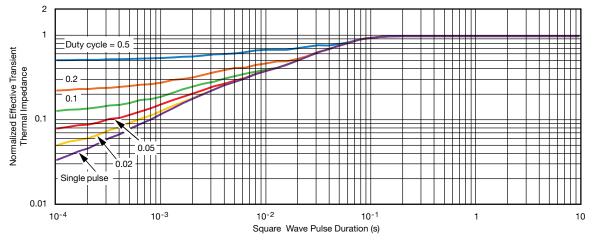
For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

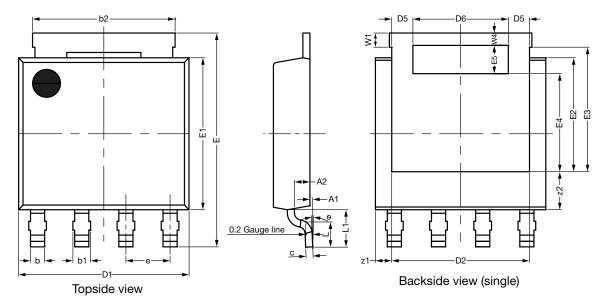
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77430.

S20-0201-Rev. A, 30-Mar-2020	5	Document Number: 77430
	For technical questions, contact: automostechsupport@vishay.con	<u>n</u>
	T TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED I	
ARE SUBJ	IECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishav.com</u>	<u>1/doc?91000</u>



PowerPAK[®] SO-8L Case Outline 3



DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
A2	0.40	0.45	0.50	0.016	0.018	0.020	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

Note

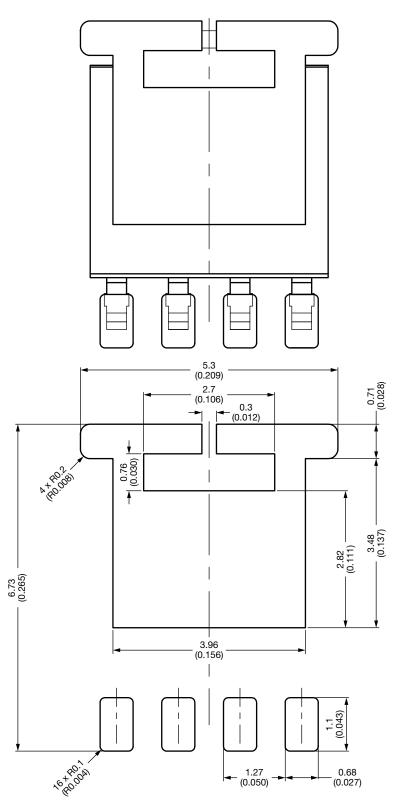
• Millimeter will govern

Revison: 05-Aug-2019

Document Number: 76666



Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)

Revision: 24-Aug-2021

Document Number: 78020



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.